



SANYO Semiconductors

## DATA SHEET

# CPH6339 — P-Channel Silicon MOSFET

## General-Purpose Switching Device Applications

### Features

- Low ON-resistance.
- High-speed switching.
- 4V drive

### Specifications

**Absolute Maximum Ratings** at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>		-45	V
Gate-to-Source Voltage	V <sub>GSS</sub>		±20	V
Drain Current (DC)	I <sub>D</sub>		-3	A
Drain Current (Pulse)	I <sub>DP</sub>	PW≤10μs, duty cycle≤1%	-12	A
Allowable Power Dissipation	P <sub>D</sub>	When mounted on ceramic substrate (900mm <sup>2</sup> ×0.8mm)	1.6	W
Channel Temperature	T <sub>ch</sub>		150	°C
Storage Temperature	T <sub>stg</sub>		-55 to +150	°C

**Electrical Characteristics** at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> =-1mA, V <sub>GS</sub> =0V	-45			V
Zero-Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-45V, V <sub>GS</sub> =0V			-1	μA
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±16V, V <sub>DS</sub> =0V			±10	μA
Cutoff Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> =-10V, I <sub>D</sub> =-1mA	-1.2		-2.6	V
Forward Transfer Admittance	y <sub>fs</sub>	V <sub>DS</sub> =-10V, I <sub>D</sub> =-1.5A	2.0	3.4		S
Static Drain-to-Source On-State Resistance	R <sub>DS(on)1</sub>	I <sub>D</sub> =-1.5A, V <sub>GS</sub> =-10V		82	107	mΩ
	R <sub>DS(on)2</sub>	I <sub>D</sub> =-1A, V <sub>GS</sub> =-4.5V		128	180	mΩ
	R <sub>DS(on)3</sub>	I <sub>D</sub> =-1A, V <sub>GS</sub> =-4V		140	196	mΩ

Marking : YR

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**SANYO Semiconductor Co., Ltd.**

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# CPH6339

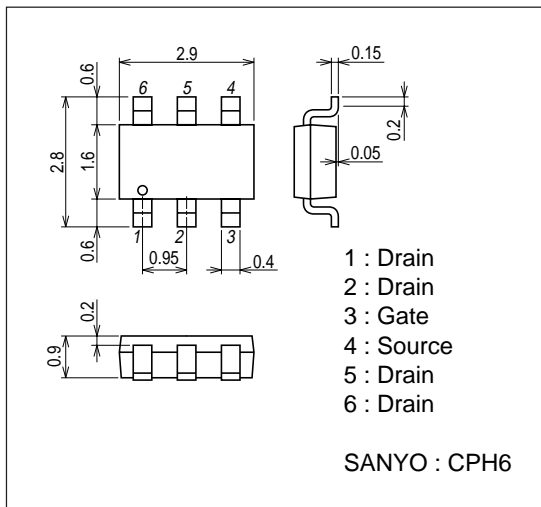
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Input Capacitance	Ciss	V <sub>DS</sub> =-20V, f=1MHz		680		pF
Output Capacitance	Coss	V <sub>DS</sub> =-20V, f=1MHz		75		pF
Reverse Transfer Capacitance	Crss	V <sub>DS</sub> =-20V, f=1MHz		50		pF
Turn-ON Delay Time	t <sub>d(on)</sub>	See specified Test Circuit.		10		ns
Rise Time	t <sub>r</sub>	See specified Test Circuit.		12		ns
Turn-OFF Delay Time	t <sub>d(off)</sub>	See specified Test Circuit.		54		ns
Fall Time	t <sub>f</sub>	See specified Test Circuit.		27		ns
Total Gate Charge	Qg	V <sub>DS</sub> =-24V, V <sub>GS</sub> =-10V, I <sub>D</sub> =-3A		14		nC
Gate-to-Source Charge	Qgs	V <sub>DS</sub> =-24V, V <sub>GS</sub> =-10V, I <sub>D</sub> =-3A		2.2		nC
Gate-to-Drain "Miller" Charge	Qgd	V <sub>DS</sub> =-24V, V <sub>GS</sub> =-10V, I <sub>D</sub> =-3A		2.9		nC
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =-3A, V <sub>GS</sub> =0V	-0.85		-1.2	V

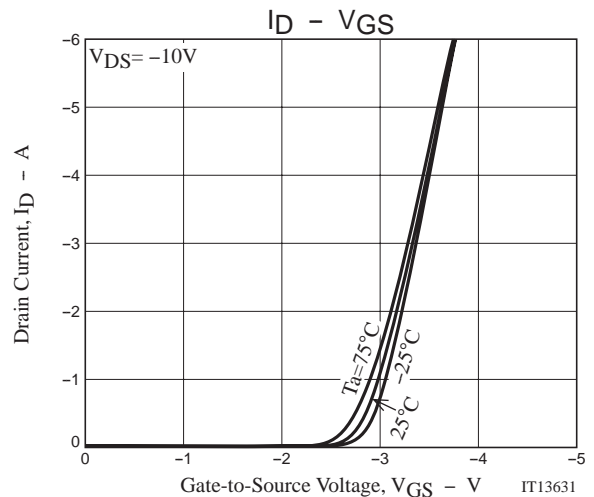
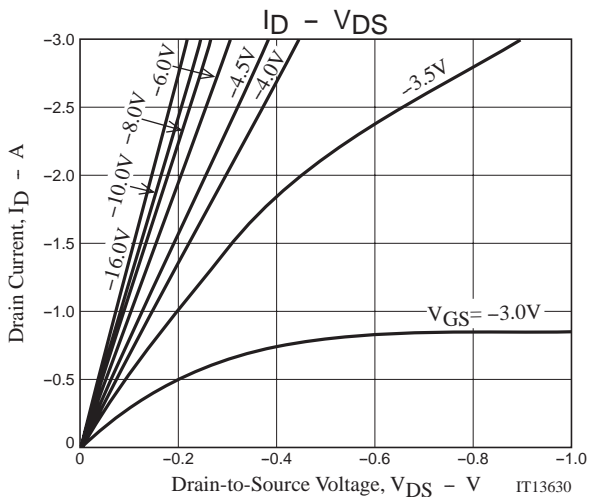
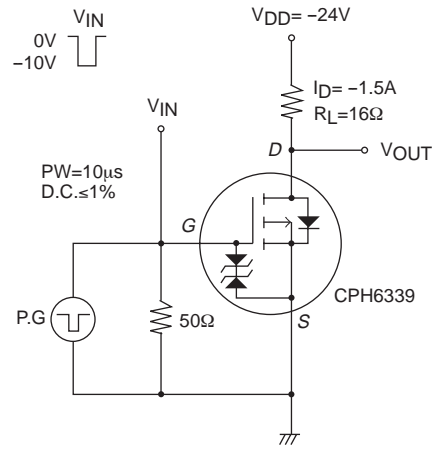
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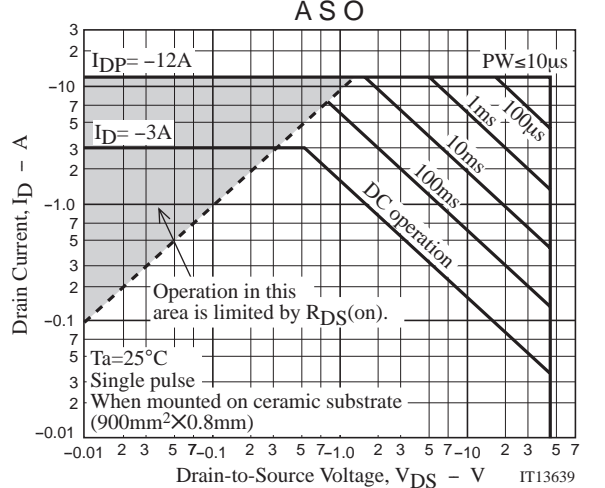
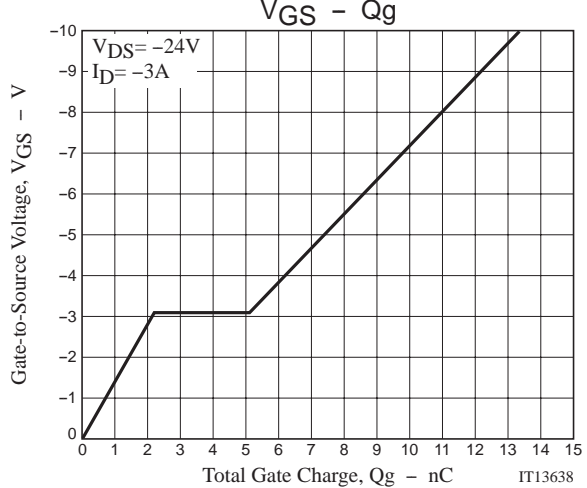
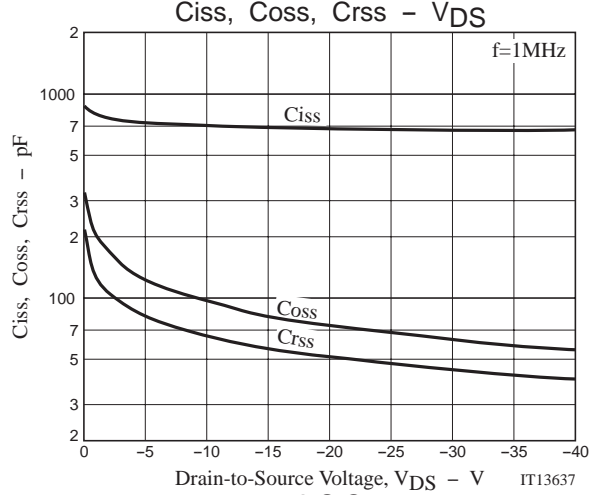
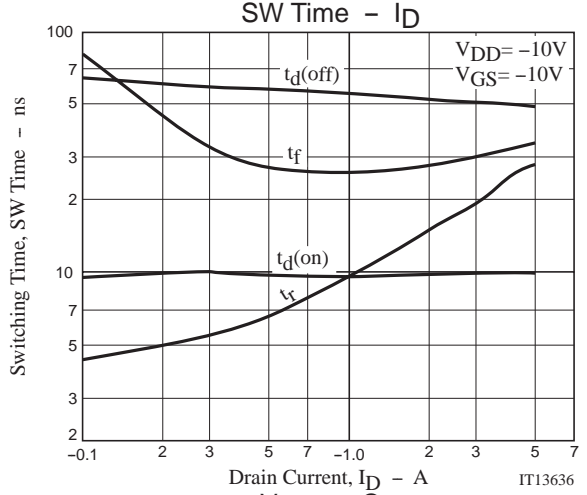
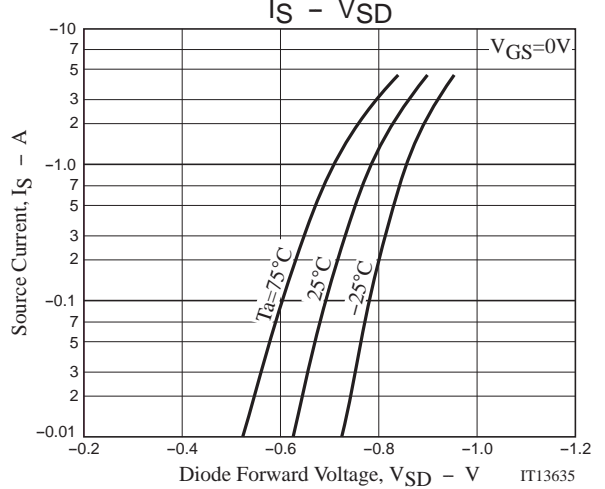
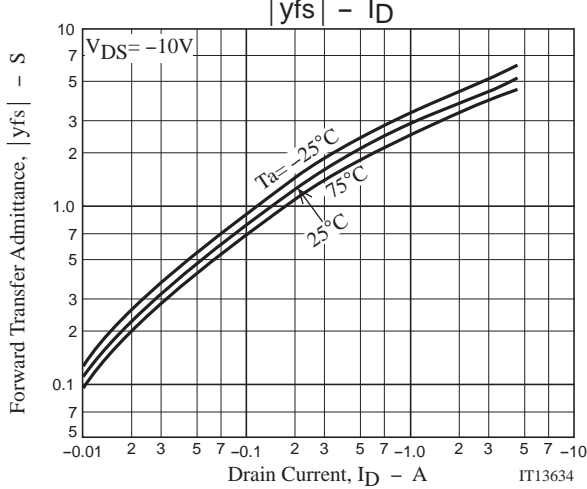
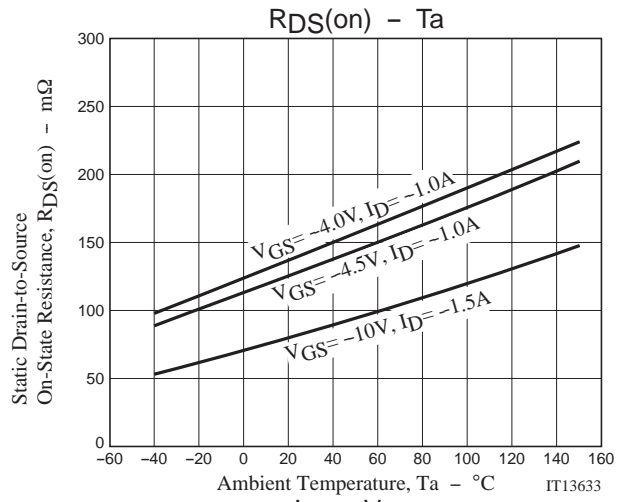
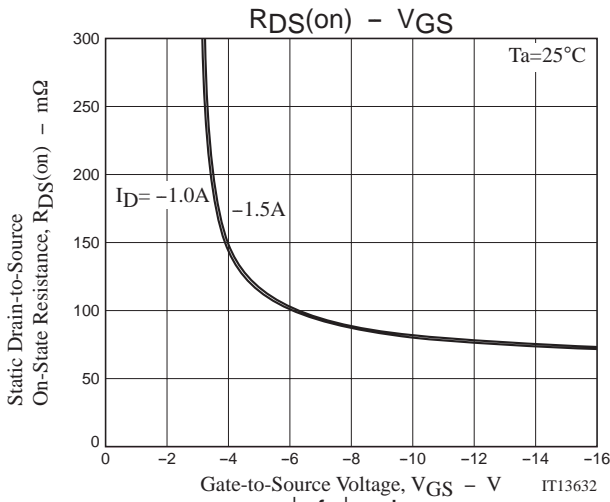
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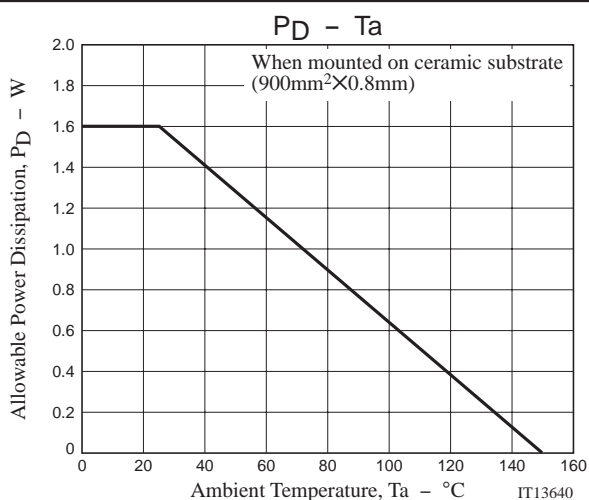
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## Switching Time Test Circuit







Note on usage : Since the CPH6339 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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